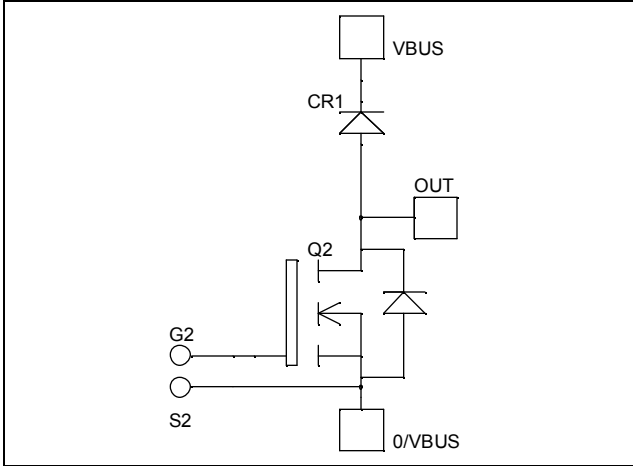


***Boost chopper  
MOSFET Power Module***

**$V_{DSS} = 1200V$   
 $R_{DSon} = 290m\Omega$  max @  $T_j = 25^\circ C$   
 $I_D = 34A$  @  $T_c = 25^\circ C$**

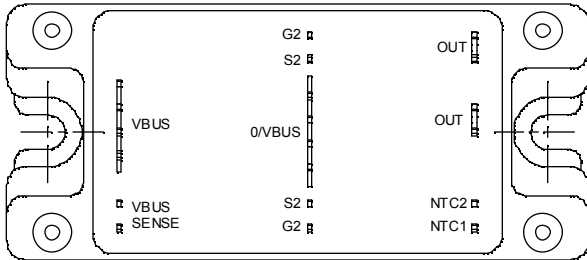


**Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

**Features**

- Power MOS 7<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	1200	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	34
		$T_c = 80^\circ C$	25
$I_{DM}$	Pulsed Drain current	136	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	290	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	780
$I_{AR}$	Avalanche current (repetitive and non repetitive)	22	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$BV_{DSS}$	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 500\mu A$	1200			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1200V$   $T_j = 25^\circ\text{C}$			200	$\mu A$
		$V_{GS} = 0V, V_{DS} = 1000V$   $T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 17A$			290	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$	3		5	V
$I_{GSS}$	Gate - Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 150$	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		10.3		nF
$C_{oss}$	Output Capacitance			1.54		
$C_{rss}$	Reverse Transfer Capacitance			0.26		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 600V$ $I_D = 34A$		374		nC
$Q_{gs}$	Gate - Source Charge			48		
$Q_{gd}$	Gate - Drain Charge			240		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V$ $V_{Bus} = 800V$ $I_D = 34A$ $R_G = 2.5\Omega$		20		ns
$T_r$	Rise Time			15		
$T_{d(off)}$	Turn-off Delay Time			160		
$T_f$	Fall Time			45		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 34A, R_G = 2.5\Omega$		1980		$\mu J$
$E_{off}$	Turn-off Switching Energy ❷			1371		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 34A, R_G = 2.5\Omega$		3131		$\mu J$
$E_{off}$	Turn-off Switching Energy ❷			1714		

## Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle   $T_c = 70^\circ\text{C}$		60		A
$V_F$	Diode Forward Voltage	$I_F = 60A$		2	2.5	V
		$I_F = 120A$		2.3		
		$I_F = 60A$   $T_j = 125^\circ\text{C}$		1.8		
$t_{rr}$	Reverse Recovery Time	$I_F = 60A$   $V_R = 800V$   $di/dt = 200A/\mu s$   $T_j = 25^\circ\text{C}$		400		ns
		$T_j = 125^\circ\text{C}$		470		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 60A$   $V_R = 800V$   $di/dt = 200A/\mu s$   $T_j = 25^\circ\text{C}$		1200		nC
		$T_j = 125^\circ\text{C}$		4000		

❶  $E_{on}$  includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case	Transistor		0.16	°C/W	
		Diode		0.9		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>isol</sub> <1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque		To Heatsink	M5	4.7	N.m
Wt	Package Weight				160	g

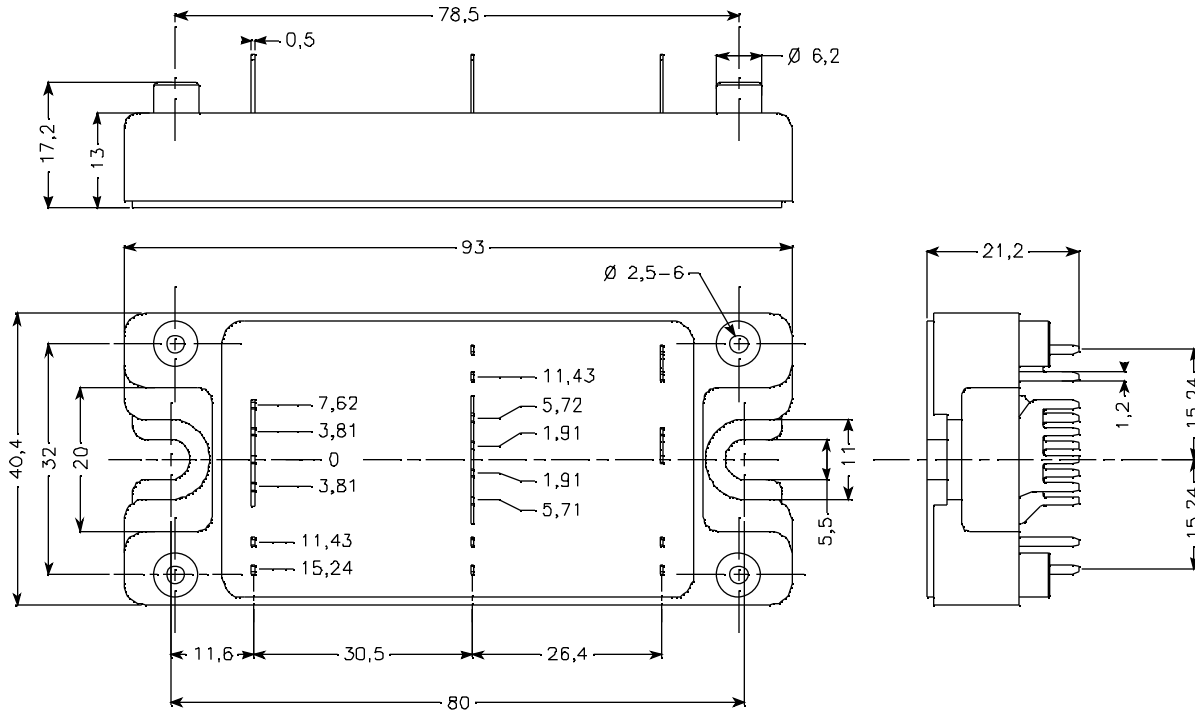
**Temperature sensor NTC**

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		68		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.16 K		4080		K

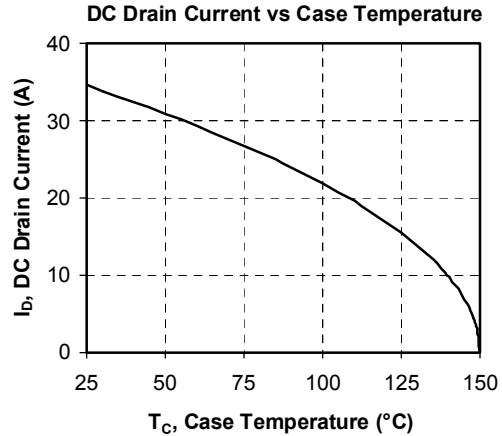
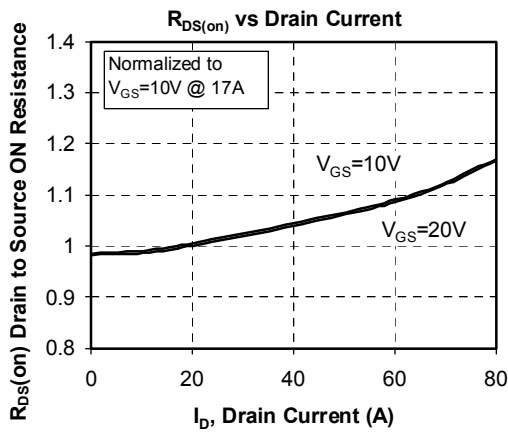
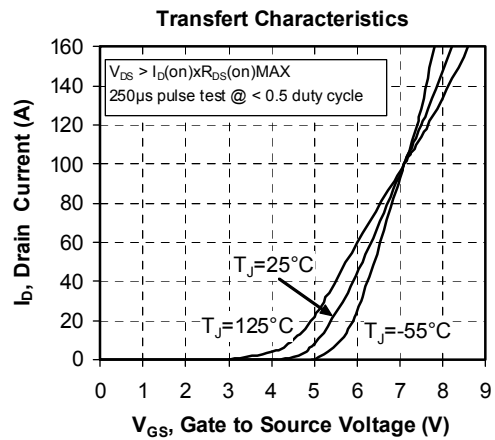
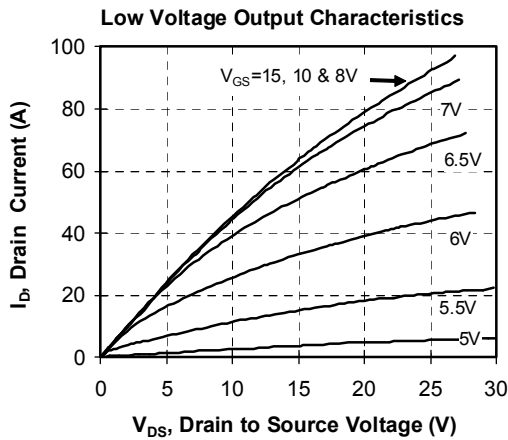
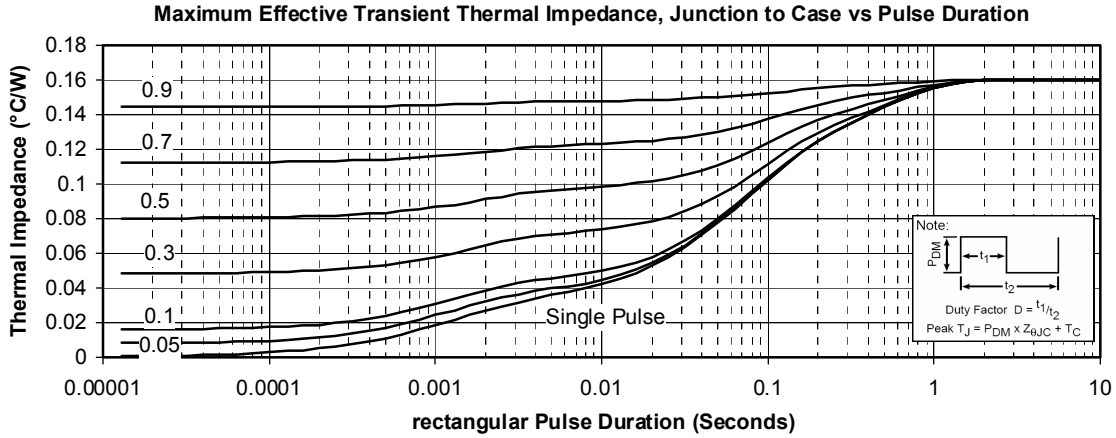
$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

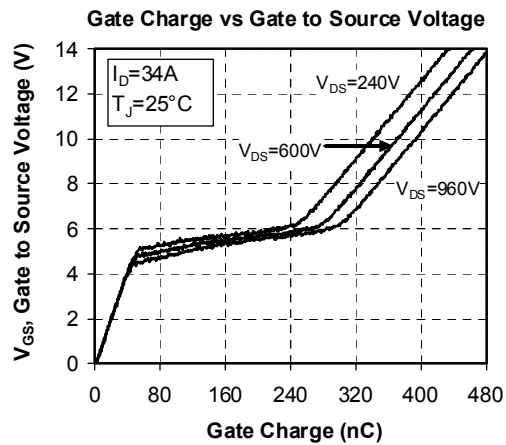
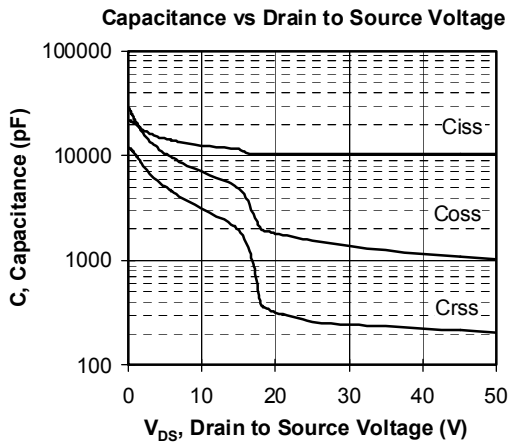
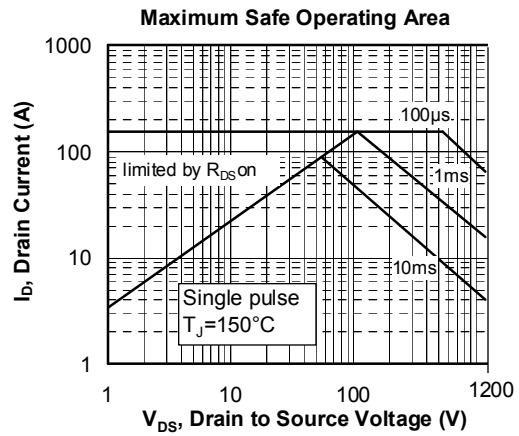
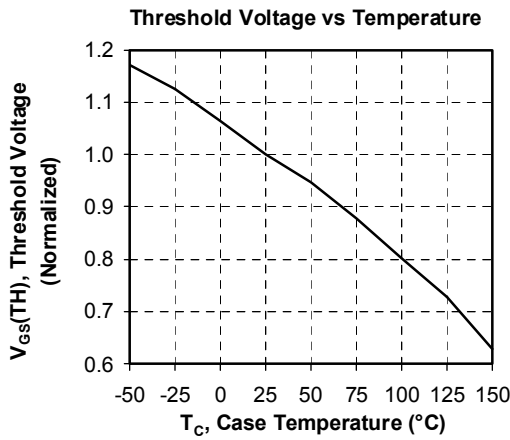
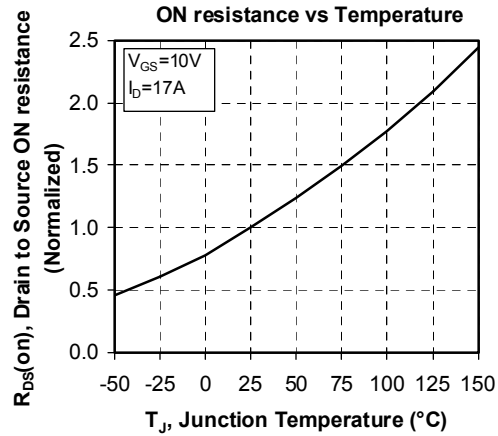
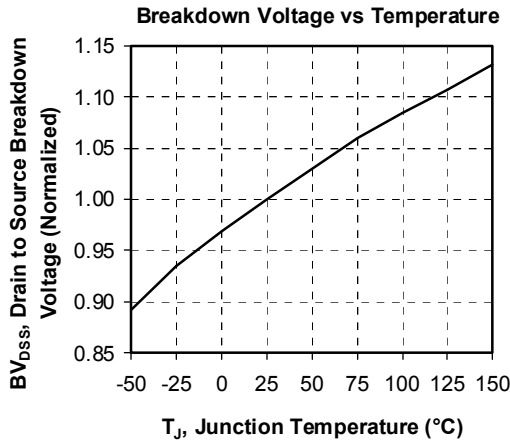
T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

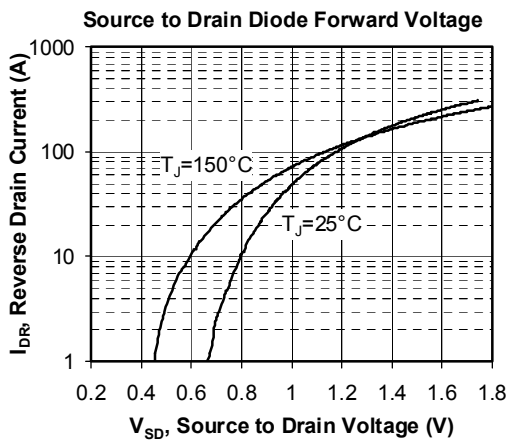
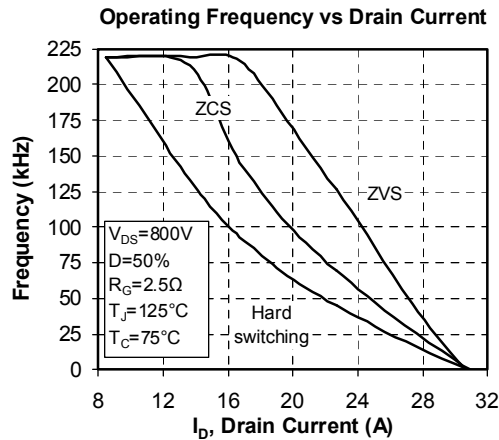
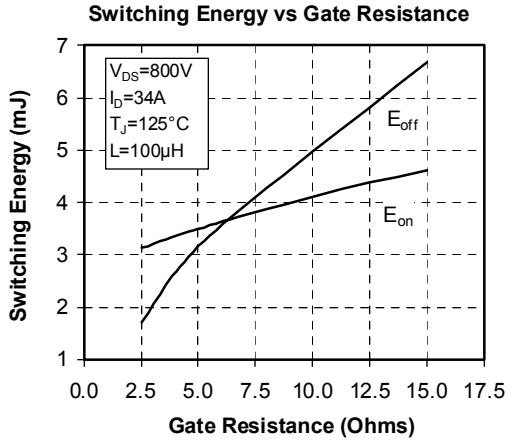
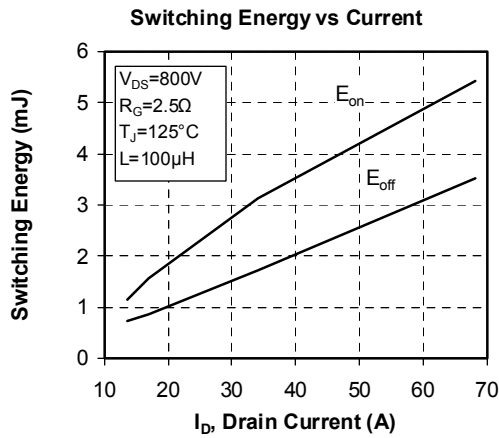
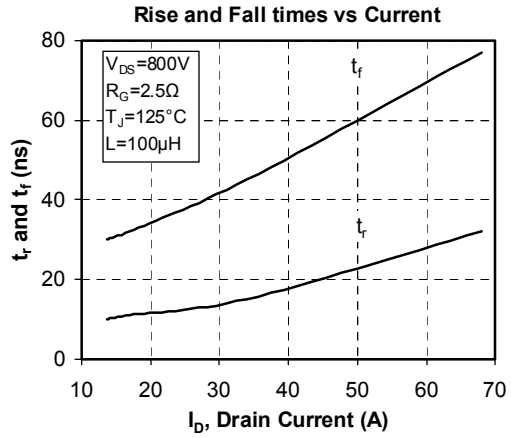
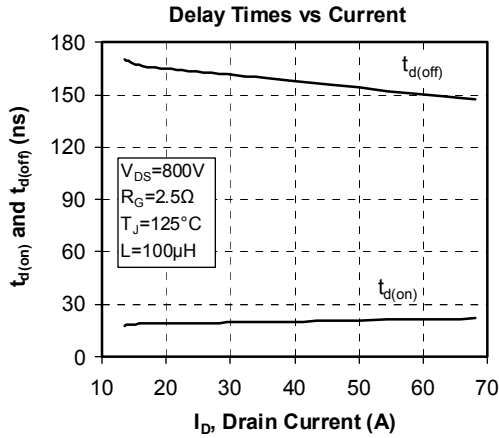
**Package outline**



**Typical Performance Curve**







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